

Silicon NPN Power Transistors

2SC3298 2SC3298A 2SC3298B

DESCRIPTION

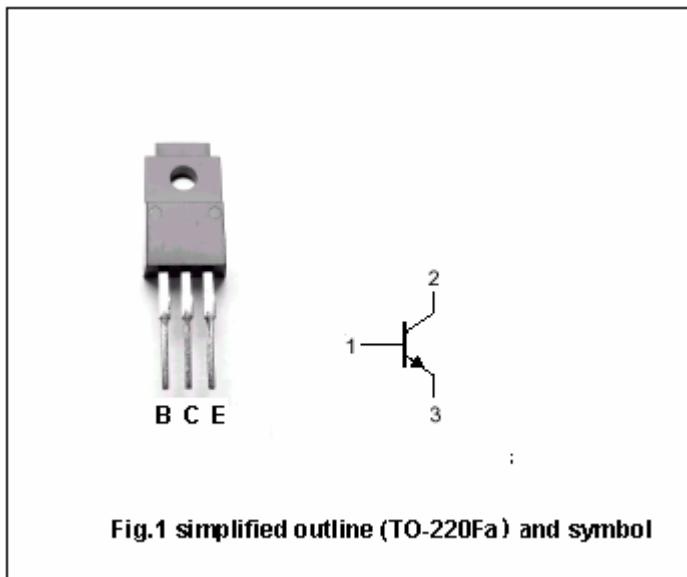
- With TO-220Fa package
- Complement to type
2SA1306,2SA1306A,2SA1306B

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SC3298	160	V
		2SC3298A	180	
		2SC3298B	200	
V _{CEO}	Collector-emitter voltage	2SC3298	160	V
		2SC3298A	180	
		2SC3298B	200	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1.5	A
I _B	Base current		0.15	A
P _C	Collector power dissipation	T _C =25°C	20	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SC3298	160			V
		2SC3298A	180			
		2SC3298B	200			
V _{CEsat}	Collector-emitter saturation voltage	I _C =0.5A, I _B =50mA			1.5	V
V _{BE}	Base-emitter voltage	I _C =0.5A, V _{CE} =5V			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =160V, I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V, I _C =0			1.0	μA
h _{FE}	DC current gain	I _C =0.1A; V _{CE} =5V	70		240	
C _{ob}	Output capacitance	I _E =0; V _{CB} =10V, f=1MHz		25		pF
f _T	Transition frequency	I _C =0.1A; V _{CE} =10V		100		MHz

◆ h_{FE} Classifications

O	Y
70-140	120-240

PACKAGE OUTLINE

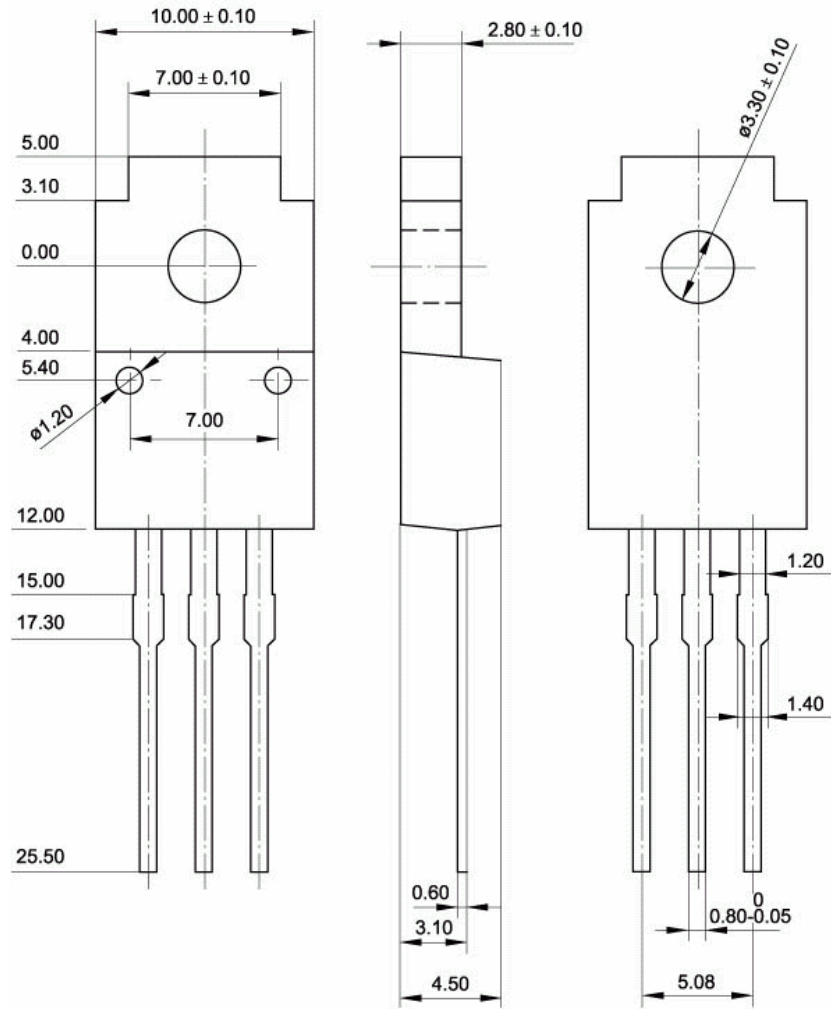


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)